

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

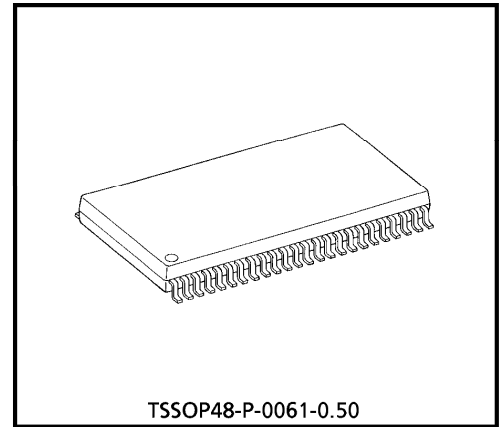
TC74VCX16244FT

LOW-VOLTAGE 16-BIT BUS BUFFER WITH 3.6V TOLERANT INPUTS AND OUTPUTS

The TC74VCX16244FT is a high performance CMOS 16-bit BUS BUFFER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation. It is also designed with over voltage tolerant inputs and outputs up to 3.6V.

This device is non-inverting 3-state buffer having four active-low output enables. It can be used as four 4-bit buffers two 8-bit buffers or one 16-bit buffer. When the \overline{OE} input is high, the outputs are in a high impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



Weight : 0.25g (Typ.)

FEATURES

- Low Voltage Operation : $V_{CC} = 1.8 \sim 3.6V$
- High Speed Operation : $t_{pd} = 2.5ns$ (max.) at $V_{CC} = 3.0 \sim 3.6V$
 : $t_{pd} = 3.0ns$ (max.) at $V_{CC} = 2.3 \sim 2.7V$
 : $t_{pd} = 5.0ns$ (max.) at $V_{CC} = 1.8V$
- 3.6V Tolerant inputs and outputs.
- Output Current : $I_{OH} / I_{OL} = \pm 24mA$ (min.) at $V_{CC} = 3.0V$
 : $I_{OH} / I_{OL} = \pm 18mA$ (min.) at $V_{CC} = 2.3V$
 : $I_{OH} / I_{OL} = \pm 6mA$ (min.) at $V_{CC} = 1.8V$
- Latch-up Performance : $\pm 300mA$
- ESD Performance : Human Body Model $> \pm 2000V$
 : Machine Model $> \pm 200V$
- Package : TSSOP
 (Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 1)

(Note 1) To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

PIN CONNECTION

$\overline{1OE}$	1	48	$\overline{2OE}$
1Y1	2	47	1A1
1Y2	3	46	1A2
GND	4	45	GND
1Y3	5	44	1A3
1Y4	6	43	1A4
V_{CC}	7	42	V_{CC}
2Y1	8	41	2A1
2Y2	9	40	2A2
GND	10	39	GND
2Y3	11	38	2A3
2Y4	12	37	2A4
3Y1	13	36	3A1
3Y2	14	35	3A2
GND	15	34	GND
3Y3	16	33	3A3
3Y4	17	32	3A4
V_{CC}	18	31	V_{CC}
4Y1	19	30	4A1
4Y2	20	29	4A2
GND	21	28	GND
4Y3	22	27	4A3
4Y4	23	26	4A4
$\overline{4OE}$	24	25	$\overline{3OE}$

(TOP VIEW)

980910EBA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

TRUTH TABLE

INPUTS		OUTPUTS
$\overline{1OE}$	1A1-1A4	1Y1-1Y4
L	L	L
L	H	H
H	X	Z

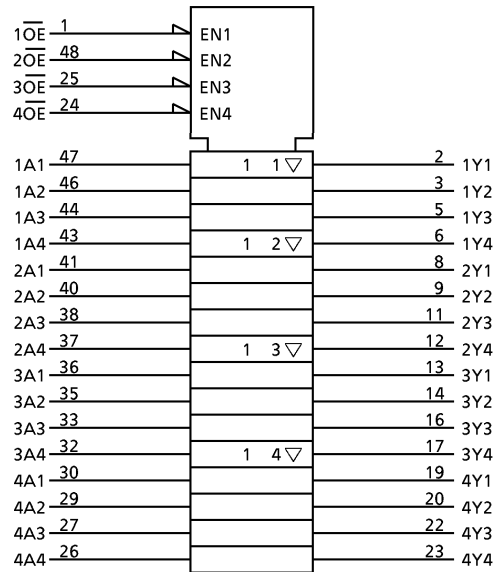
INPUTS		OUTPUTS
$\overline{2OE}$	1A1-2A4	2Y1-2Y4
L	L	L
L	H	H
H	X	Z

INPUTS		OUTPUTS
$\overline{3OE}$	3A1-3A4	3Y1-3Y4
L	L	L
L	H	H
H	X	Z

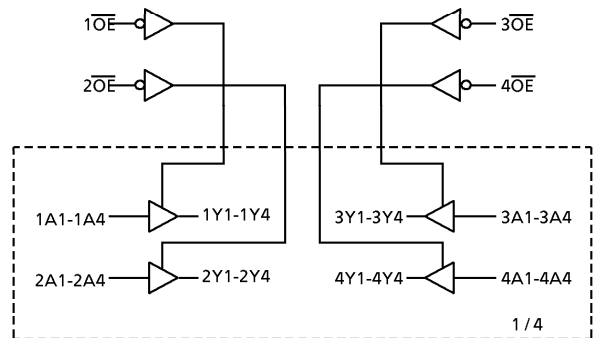
INPUTS		OUTPUTS
$\overline{4OE}$	4A1-4A4	4Y1-4Y4
L	L	L
L	H	H
H	X	Z

X : Don't Care
Z : High impedance

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



980910EBA2'

- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~4.6	V
DC Input Voltage	V_{IN}	-0.5~4.6	V
DC Output Voltage	V_{OUT}	-0.5~4.6 (Note 1)	V
		-0.5~ V_{CC} + 0.5 (Note 2)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC} / I_{GND}	±100	mA
Storage Temperature	T_{stg}	-65~150	°C

(Note 1) Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3) $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	V_{OUT}	0~3.6 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH} / I_{OL}	±24 (Note 7)	mA
		±18 (Note 8)	
		±6 (Note 9)	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt / dv	0~10 (Note 10)	ns / V

(Note 4) Data Retention Only

(Note 5) Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6V$

(Note 8) $V_{CC} = 2.3 \sim 2.7V$

(Note 9) $V_{CC} = 1.8V$

(Note 10) $V_{IN} = 0.8 \sim 2.0V$, $V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.7V < V_{CC} ≤ 3.6V)

PARAMETER		SYMBOL	TEST CONDITION		V _{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			2.7~3.6	2.0	—	V
	"L" Level	V _{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12mA	2.7	2.2	—	
				I _{OH} = -18mA	3.0	2.4	—	
				I _{OH} = -24mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	2.7~3.6	—	0.2	V
				I _{OL} = 12mA	2.7	—	0.4	
				I _{OL} = 18mA	3.0	—	0.4	
				I _{OL} = 24mA	3.0	—	0.55	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6V		2.7~3.6	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6V		2.7~3.6	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6V		2.7~3.6	—	± 20.0	
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6V		2.7~3.6	—	750	μA

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.3V ≤ VCC ≤ 2.7V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
					2.3~2.7			
Input Voltage	"H" Level	V _{IH}			2.3~2.7	1.6	—	V
	"L" Level	V _{IL}			2.3~2.7	—	0.7	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6mA	2.3	2.0	—	
				I _{OH} = -12mA	2.3	1.8	—	
				I _{OH} = -18mA	2.3	1.7	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	2.3~2.7	—	0.2	V
				I _{OL} = 12mA	2.3	—	0.4	
I _{OL} = 18mA				2.3	—	0.6		
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6V		2.3~2.7	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6V		2.3~2.7	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6V _{CC}		2.3~2.7	—	± 20.0	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 1.8V ≤ VCC < 2.3V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}	—	V
	"L" Level	V _{IL}			1.8~2.3	—	0.2 × V _{CC}	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -6mA	1.8	1.4	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	V
				I _{OL} = 6mA	1.8	—	0.3	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6V		1.8	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6V		1.8	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6V		1.8	—	± 20.0	

AC characteristics (Ta = -40~85°C, Input t_r = t_f = 2.0ns, C_L = 30pF, R_L = 500Ω)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
Propagation Delay Time	t _{pLH} t _{pHL}	(Fig.1, 2)			1.8	1.5	5.0	ns
					2.5 ± 0.2	1.0	3.0	
					3.3 ± 0.3	0.8	2.5	
3-State Output Enable Time	t _{pZL} t _{pZH}	(Fig.1, 3)			1.8	1.5	6.5	ns
					2.5 ± 0.2	1.0	4.1	
					3.3 ± 0.3	0.8	3.5	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	(Fig.1, 3)			1.8	1.5	5.0	ns
					2.5 ± 0.2	1.0	3.8	
					3.3 ± 0.3	0.8	3.5	
Output To Output Skew	t _{osLH} t _{osHL}	(Note 11)			1.8	—	0.5	ns
					2.5 ± 0.2	—	0.5	
					3.3 ± 0.3	—	0.5	

For C_L = 50pF, add approximately 300ps to the AC maximum specification.

(Note 11) Parameter guaranteed by design.
(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)

Dynamic switching characteristics (Ta = 25°C, Input tr = tf = 2.0ns, CL = 30pF)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Quiet Output Maximum Dynamic VOL	VOLP	VIH = 1.8V, VIL = 0V (Note 12)	1.8	0.25	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	0.6	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	0.8	
Quiet Output Minimum Dynamic VOL	VOLV	VIH = 1.8V, VIL = 0V (Note 12)	1.8	-0.25	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	-0.6	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	-0.8	
Quiet Output Minimum Dynamic VOH	VOHV	VIH = 1.8V, VIL = 0V (Note 12)	1.8	1.5	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	1.9	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	2.2	

(Note 12) Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

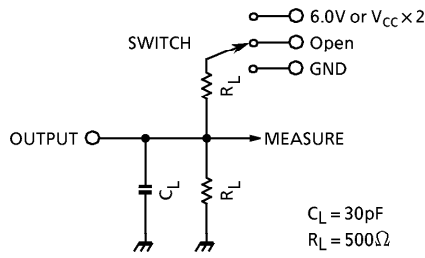
PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Input Capacitance	CIN		1.8, 2.5, 3.3	6	pF
Output Capacitance	CO		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	CPD	fIN = 10MHz (Note 13)	1.8, 2.5, 3.3	20	pF

(Note 13) CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16 \text{ (per bit)}$$

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0V @ $V_{CC} = 3.3 \pm 0.3V$ $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2V$ @ $V_{CC} = 1.8V$
t_{pHZ}, t_{pZH}	GND

AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}

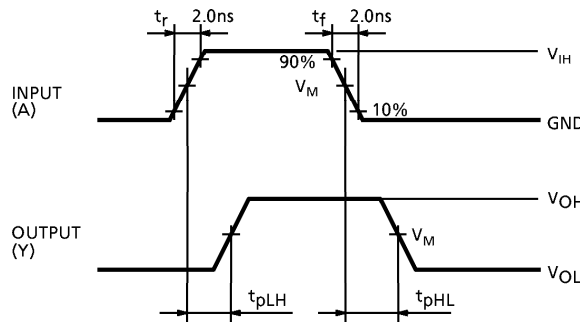
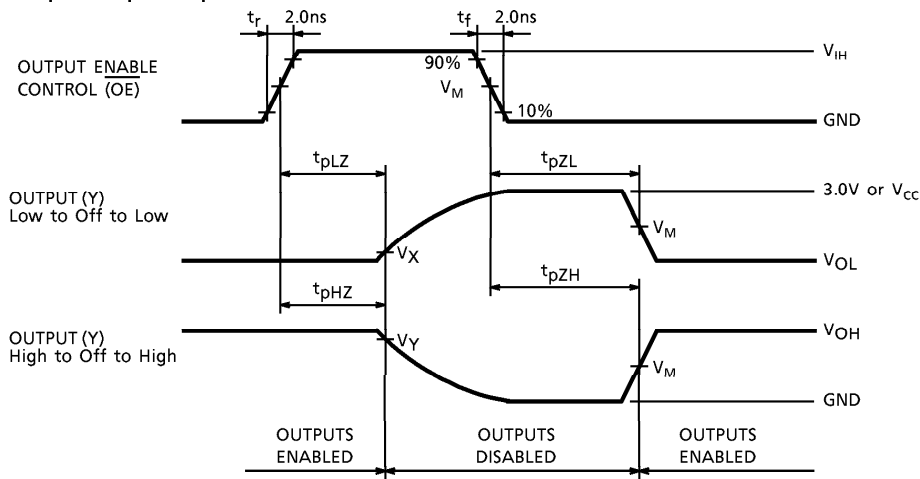


Fig.3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

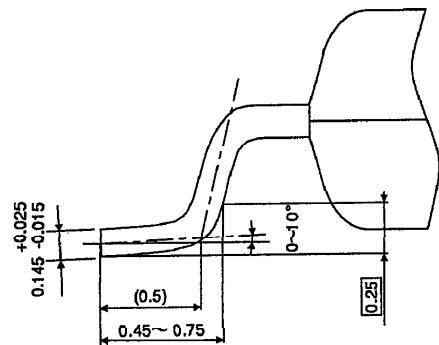
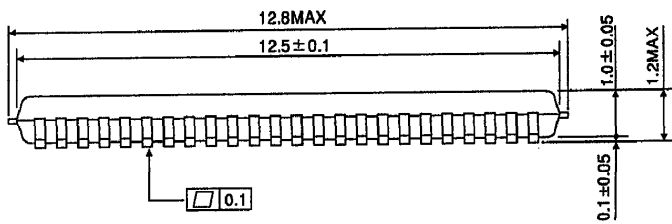
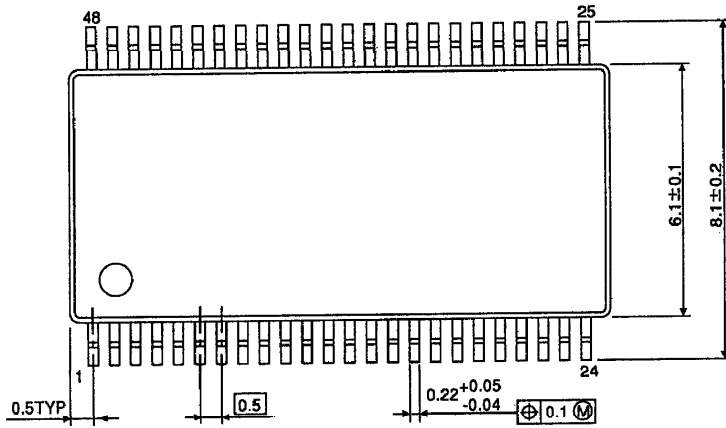


SYMBOL	V_{CC}		
	$3.3 \pm 0.3V$	$2.5 \pm 0.2V$	1.8V
V_{IH}	2.7V	V_{CC}	V_{CC}
V_M	1.5V	$V_{CC} / 2$	$V_{CC} / 2$
V_X	$V_{OL} + 0.3V$	$V_{OL} + 0.15V$	$V_{OL} + 0.15V$
V_Y	$V_{OH} - 0.3V$	$V_{OH} - 0.15V$	$V_{OH} - 0.15V$

OUTLINE DRAWING

TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25g (Typ.)